

L1200-35T52 High Power InGaAsP IR LED

L1200-35T52 is InGaAsP LED mounted on TO-18 stem and hermetically sealed with flat glass can.

On forward bias it emits a spectral band of radiation, which peaks at 1200nm.

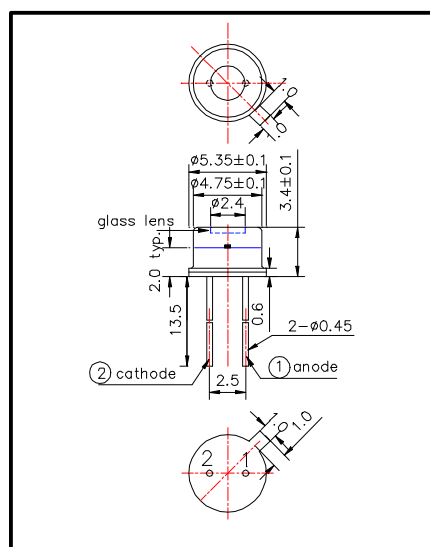
Features

- 1) Wide viewing angle
- 2) High Reliability
- 3) 350micron sq. die

Specifications

- | | |
|---------------------|-----------------------|
| 1) Product Name | NIR LED Lamp |
| 2) Type No. | L1200-35T52 |
| 3) Chip Spec. | |
| (1) Material | InGaAsP/InP |
| (2) Peak Wavelength | 1200nm |
| 4) Package | |
| (1) Type | TO-18 stem |
| (2) Lens | f 2.4 flat glass lens |
| (3) Cap | Gold plated |

Outer dimension(Unit:mm)



Absolute Maximum Ratings

Item	Symbol	Maximum Rated Value	Unit	Ambient Temperature
Power Dissipation	P _D	120	mW	T _a =25°C
Forward Current	I _F	100	mA	T _a =25°C
Pulse Forward Current	I _{FP}	1000	mA	T _a =25°C
Reverse Voltage	V _R	5	V	T _a =25°C
Operating Temperature	T _{OPR}	-30 ~ +80	°C	
Storage Temperature	T _{STG}	-30 ~ +100	°C	
Soldering Temperature	T _{SOL}	260	°C	

‡ Pulse Forward Current condition: Duty=1% and Pulse Width=1us.

‡ Soldering condition: Soldering condition must be completed within 3 seconds at 260°C

Electro-Optical Characteristics

Item	Symbol	Condition	Minimum	Typical	Maximum	Unit
Forward Voltage	V _F	I _F =20mA		0.8	1.3	V
Reverse Current	I _R	V _R =5V			10	uA
Total Radiated Power	P _O	I _F =20mA		0.1		mW
Peak Wavelength	λ _P	I _F =20mA	1150	1200	1250	nm
Half Width	Δλ	I _F =20mA		100		nm
Viewing Half Angle	Q _{1/2}	I _F =20mA		±55		deg.
Rise Time	t _r	I _F =20mA		10		ns
Fall Time	t _f	I _F =20mA		10		ns

‡ Radiated Power is measured by Ando Optical Multi Meter AQ2140 & AQ2742